

# **Small Signal Diode**



### **Features**

- ♦Surface device type mounting
- ♦Moisture sensitivity level 1
- ♦Matte Tin(Sn) lead finish with Nickel(Ni) underplate
- ♦Pb free version and RoHS compliant

### **Mechanical Data**

- ♦Case :SOT-23 small outline plastic package
- ♦Terminal: Matte tin plated, lead free., solderable per MIL-STD-202, Method 208 guaranteed
- ♦High temperature soldering guaranteed: 260°C/10s
- ♦Weight : 0.008gram (approximately)
- ♦ Marking Code : A1,A4,A7

# A E F G

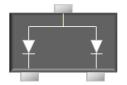
**BAW56, BAV70, BAV99** 

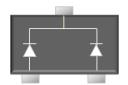
**SOT-23** 

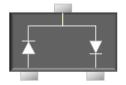
225mW SMD Switching Diode

Dimensions	Unit (mm)		Unit (inch)	
Difficusions	Min	Max	Min	Max
Α	2.80	3.00	0.110	0.118
В	1.20	1.40	0.047	0.055
С	0.30	0.50	0.012	0.020
D	1.80	2.00	0.071	0.079
E	2.25	2.55	0.089	0.100
F	0.90	1.20	0.035	0.047
G	0.550 REF		0.022 REF	
Н	0.08	0.19	0.003	0.010

# **Pin Configuration**





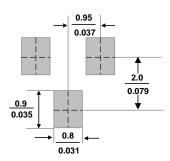


BAW56 BAV70 BAV99

### **Ordering Information**

Package	Part No.	Packing	Marking
SOT-23	BAW56 RF	3K / 7" Reel	A1
SOT-23	BAV70 RF	3K / 7" Reel	A4
SOT-23	BAV99 RF	3K / 7" Reel	A7
SOT-23	BAW56 RFG	3K / 7" Reel	A1
SOT-23	BAV70 RFG	3K / 7" Reel	A4
SOT-23	BAV99 RFG	3K / 7" Reel	A7

# **Suggested PAD Layout**



# **Maximum Ratings and Electrical Characteristics**

Rating at 25°C ambient temperature unless otherwise specified.

## Maximum Ratings

Maximum Ratings					
Type Number	Symbol	Value	Units		
Power Dissipation	P□	225	mW		
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	70	V		
Repetitive Peak Forward Current	IFRМ	450	mA		
Mean Forward Current	lo	200	mA		
Non-Repetitive Peak Forward Pulse Width=1 sec		0.5	А		
Surge Current Pulse Width=1 µse	C IFSM	2			
Thermal Resistance (Junction to Ambient)	RθJA	357	°C/W		
Junction and Storage Temperature Range	TJ, Tstg	-55 to + 150	°C		



# BAW56, BAV70, BAV99 225mW SMD Switching Diode

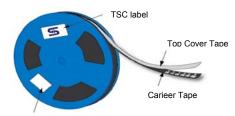
# **Small Signal Diode**

### **Electrical Characteristics**

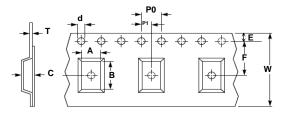
Rating at 25°C ambient temperature unless otherwise specified.

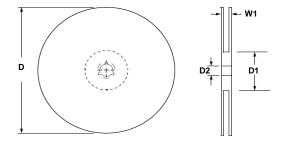
Type Number			Symbol	Min	Max	Units
Reverse Breakdown Voltage	I <sub>R</sub> =	100μΑ	V <sub>(BR)</sub>	70	-	V
Forward Voltage	I <sub>F</sub> =	50mA	VF	-	1.00	V
	I <sub>F</sub> =	150mA		-	1.25	V
Reverse Leakage Current	V <sub>R</sub> =	70V	lR	-	2.50	μΑ
Junction Capacitance	V <sub>R</sub> = 0\	/, f=1.0MHz	Cı	-	1.5	pF
Reverse Recovery Time	$I_F = I_R = 10 \text{mA}, R_L = 100 \Omega$	, I <sub>RR</sub> =1mA	Trr	-	6.0	ns

# Tape & Reel specification

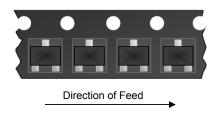


Any Additional Label (If Required)





Item	Symbol	Dimension(mm)
Carrier width	Α	3.15 ±0.10
Carrier length	В	2.77 ±0.10
Carrier depth	С	1.22 ±0.10
Sprocket hole	d	1.50 ± 0.10
Reel outside diameter	D	178 ± 1
Reel inner diameter	D1	55 Min
Feed hole width	D2	13.0 ± 0.20
Sprocke hole position	E	1.75 ±0.10
Punch hole position	F	3.50 ±0.05
Sprocke hole pitch	P0	4.00 ±0.10
Embossment center	P1	2.00 ±0.05
Overall tape thickness	Т	0.229 ±0.013
Tape width	W	8.10 ±0.20
Reel width	W1	12.30 ±0.20

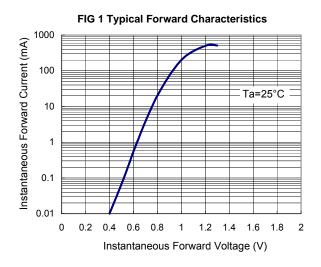




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# **Small Signal Diode**

# **Rating and Characteristic Curves**

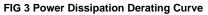


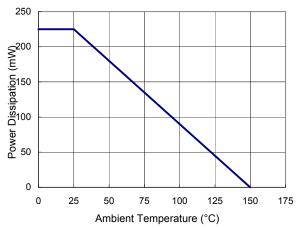
Temperature.

10000
VR=20V
Typical
100
0 20 40 60 80 100 120 140 160 180 200

Junction Temperature (°C)

FIG 2 Leakage Current vs Junction





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BAV70 BAV99 BAW56